

# Zero-Voltage-Switching Single-Phase Inverter with Active Power Decoupling

Zhengyu Ye, Yanan Chen, Dehong Xu

Institute of Power Electronic  
Zhejiang University  
Hangzhou, China  
21510176@zju.edu.cn

**Abstract**—Active Power Decoupling (APD) is used for single-phase inverter to cope with the double-line frequency power pulsation in the inverter DC side. In this paper, zero-voltage switching (ZVS) for the single-phase inverter with APD is introduced. A ZVS SPWM scheme for single-phase inverter with APD is proposed. The operation of the ZVS single-phase inverter with APD is analyzed and ZVS conditions are derived. Finally, a 500kHz 1.5kW prototype is built to verify the theoretical analysis.

**Keywords**—single-phase inverter; Zero-Voltage-Switching; Active Power Decoupling

## I. INTRODUCTION

Single-phase inverters are widely used in residential photovoltaic power generations applications. Since there is double-line frequency power pulsation in the DC side of inverter, generally a large electrolytic capacitor is needed at DC bus of PV inverter. It not only decreases the power density, but also may affect the reliability of the inverter due to the short expectancy of the electrolytic capacitor. Various Active Power Decoupling (APD) methods have been investigated by predecessors [1]-[5]. APD composes power converter and smaller capacitor to take the function of power buffer for double-line frequency power pulsation, therefore it decouples double-line frequency power coupling between grid and DC bus of inverter. Among them a buck-type topology [5] is widely used, shown in Fig. 1.

Soft switching has been studied to increase the power density and efficiency of inverters. Soft switching was originally introduced to the inverter by using the resonant DC link concept by Prof. Deepak Divan [6][7]. Later ZVS SVM

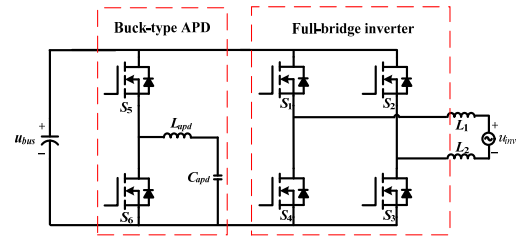


Fig. 1. Single-phase inverter with buck-type APD

is invented for the three-phase grid inverter, which combines advantage of PWM inverter and soft-switching concept [8]. A ZVS single-phase inverter is proposed in [9] and a ZVS-SPWM scheme is proposed in [10]. With introduction of soft switching and SiC MOSFET, higher efficiency and filter size reduction for the grid inverter are obtained [11]. Up to now, there is no report about soft-switching technology for single-phase ZVS inverter with APD.

In this paper, soft switching technique for single-phase ZVS inverter with APD is studied. Novel ZVS SPWM modulation scheme for single-phase inverter with APD is proposed. By introducing one auxiliary circuit, all switches in both inverter stage, APD stage and auxiliary branch realize ZVS. The operation of the ZVS inverter with APD is analyzed and the ZVS conditions are derived. Finally, experimental results of a 500kHz 1.5kW ZVS APD inverter with inductive load are presented to verify the proposed ZVS modulation scheme.

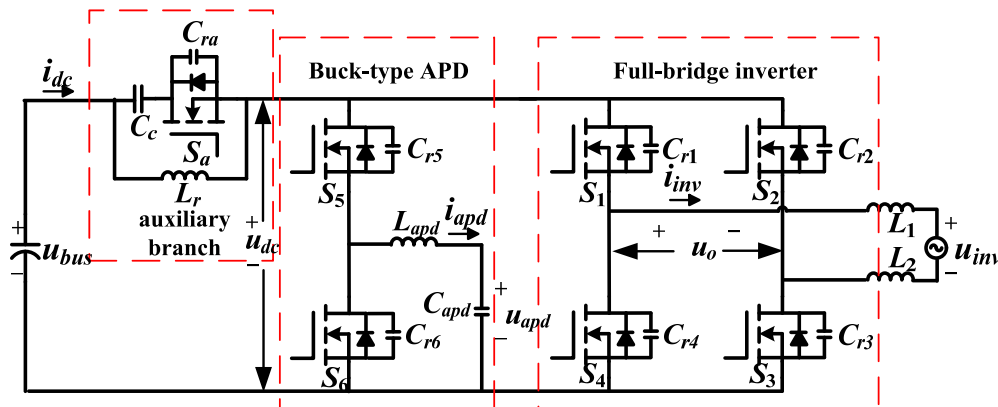


Fig. 2. Proposed ZVS inverter with APD

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## II. CIRCUIT AND ZERO-VOLTAGE-SWITCHING MODULATION FOR INVERTER WITH APD

The ZVS inverter with APD is shown in Fig. 2. An auxiliary branch is introduced to the single-phase inverter with buck-type APD. The auxiliary branch consists of auxiliary switch  $S_a$ , clamping capacitor  $C_c$  and resonant inductor  $L_r$ . Resonant capacitors  $C_{r1} \sim C_{r6}$  and  $C_{ra}$  are paralleled respectively to  $S_1 \sim S_6$  and  $S_a$

The output voltage and current of the single-phase inverter  $u_{inv}(t)$  and  $i_{inv}(t)$  can be expressed as

$$u_{inv}(t) = U \sin(\omega t) \quad i_{inv}(t) = I \sin(\omega t + \Phi) \quad (1)$$

$U$  is the voltage amplitude,  $I$  is the current amplitude,  $\omega = 2\pi f$ ,  $f$  is the fundamental frequency,  $\Phi$  is the power factor.

According to [5], the voltage of APD capacitor  $u_{apd}$  and current of APD inductor  $i_{apd}$  are represented by:

$$u_{apd}(t) = \sqrt{\frac{UI \sin(2\omega t + \Phi)}{2\omega C_{apd}} + \left(\frac{u_{bus}}{\sqrt{2}}\right)^2}$$

$$i_{apd}(t) = \frac{\frac{1}{2}UI \cos(2\omega t + \Phi)}{\sqrt{\frac{UI \sin(2\omega t + \Phi)}{2\omega C_{apd}} + \left(\frac{u_{bus}}{\sqrt{2}}\right)^2}} \quad (2)$$

In hard switching case, the inverter stage and APD stage may be controlled as shown in Fig. 3. The inverter stage is controlled by double-frequency SPWM. The modulation waveform of the inverter stage is  $u_{inv}(t)$  and  $-u_{inv}(t)$ . The triangular carrier waveform is  $u_{c1}$ , and its amplitude is  $-u_{bus} \sim +u_{bus}$ . The modulation waveform of APD stage is  $u_{apd}(t)$ . The triangular carrier is  $u_{c2}$ , and its amplitude is  $0 \sim u_{bus}$ . The frequency of  $u_{c2}$  is twice of  $u_{c1}$ .

There are two kinds of current commutation in switch bridge. One type of the commutation is from the body diode of a MOSFET to the another MOSFET in the same phase leg shown in Fig. 4 (a). It can cause higher loss in both the MOSFET to be turned on and the diode to be turned off. The another type of the commutation is from a MOSFET to the body diode of the another MOSFET in the same phase leg as

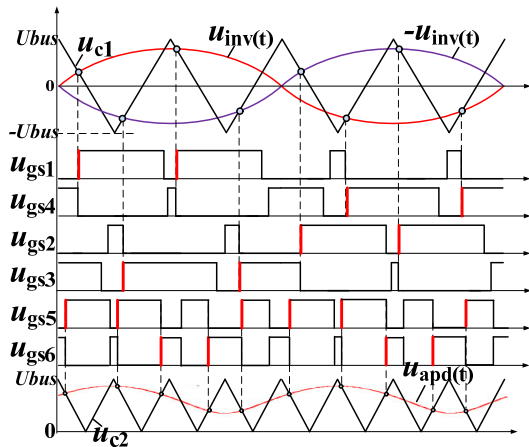


Fig. 3. Hard switching drive signals for inverter and APD

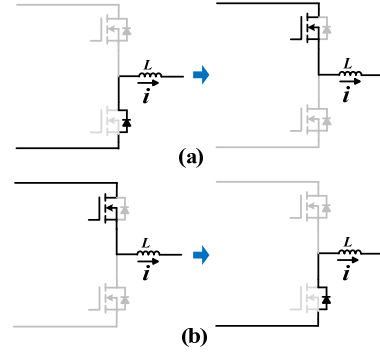


Fig. 4. Current commutation (a) from body diode to MOSFET and (b) from MOSFET to body diode

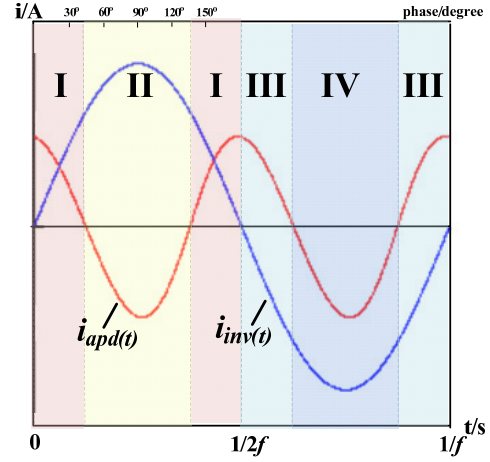


Fig. 5. Polarity of inverter current  $i_{inv}$  and APD current  $i_{apd}$  in one grid cycle

shown in Fig. 4 (b). Actually ZVS turn-off is realized for the MOSFET to be turned off and ZVS turn-on is realized for the body diode to be turned on. Therefore switching loss is significantly reduced.

The commutation from body diode to MOSFET in inverter stage and APD stage is different according to the polarity of inverter output current  $i_{inv}$  and APD inductor current  $i_{apd}$ . One grid cycle of inverter output current  $i_{inv}$  can be divided into four regions, as shown in Fig. 5, and the commutation process from body diode to MOSFET in different regions is summarized in Table I.

TABLE I COMMUTATIONS FROM BODY DIODE TO MOSFET

Region	$i_{inv}$	$i_{apd}$	inverter	APD
I	>0	>0	$D_4$ to $S_1$ $D_2$ to $S_3$	$D_6$ to $S_5$
II		<0		$D_5$ to $S_6$
III	<0	>0	$D_1$ to $S_4$ $D_3$ to $S_2$	$D_6$ to $S_5$
IV		<0		$D_5$ to $S_6$

In Fig. 3, it is observed that the commutation instants from the body-diode to the MOSFET (marked with red color) of APD stage and inverter stage are not synchronized with symmetrical triangular carrier. In order to realize ZVS turn-off of body diode and ZVS turn-on of MOSFET, the DC side voltage  $u_{dc}$  should be discharged to zero by the auxiliary

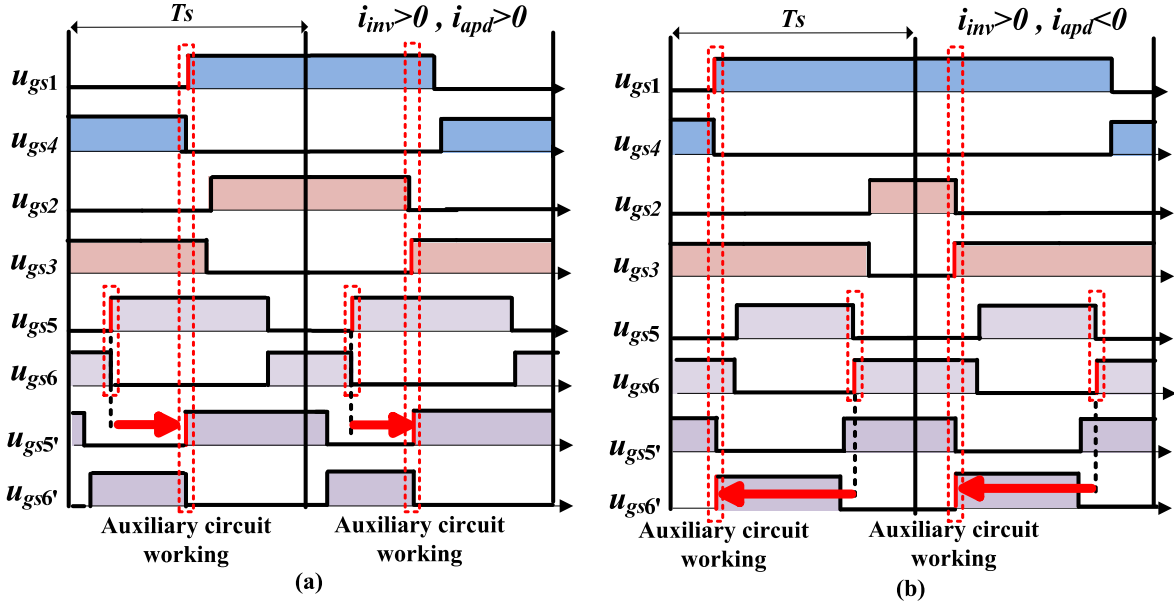


Fig. 6. Synchronize PWM edge of APD stage with inverter stage in (a) Region I and (b) Region II

branch and the switching action of  $S_a$  is activated during every commutation from body-diode to MOSFET. The auxiliary branch has to operate multiple times to realize ZVS turn-on of all switches because the commutations with the body-diode in inverter stage and APD stage are asynchronous.

In order to reduce the switching action of auxiliary switch  $S_a$ , the commutation from the body diode to the MOSFET in APD stage is synchronized with inverter stage by shifting PWM edge of  $u_{gs5}$  and  $u_{gs6}$  to  $u_{gs5}'$  and  $u_{gs6}'$ . The process in Region I and Region II is shown in Fig. 6 (a)(b),  $T_s$  is the switching period. The carrier frequency of APD stage is twice of inverter stage. Without changing the pulse width of both the inverter stage and APD stage, ZVS SPWM modulation ensures that the auxiliary branch only needs to operate once during each switching period.

### III. ANALYSIS OF ZVS CONDITION

The equivalent circuits in a switching period in Region I ( $i_{inv} > 0, i_{apd} > 0$ ) are shown in Fig. 7, and the key waveforms are shown in Fig. 8.  $u_{sc}$  is the short-circuit signal added to all switches in Stage 5. The operation stages are analyzed as follows.

**Stage 1 (freewheel,  $t_0 \sim t_1$ ):** the output current  $i_{inv}$  is freewheeling through the main switches  $S_3$  and  $S_4$ . APD inductor current  $i_{apd}$  is freewheeling through  $S_6$ . This stage is finished by turning off the main switch  $S_4$  and  $S_6$ .

**Stage 2 (freewheel,  $t_1 \sim t_2$ ):** the main switch  $S_4$  and  $S_6$  are turned off at  $t_1$  by SPWM. Output current  $i_{inv}$  is freewheeling through  $D_4$  and  $S_3$ ,  $i_{apd}$  is freewheeling through  $D_6$ . This stage is finished by turning off the auxiliary switch  $S_a$ .

**Stage 3 (resonance,  $t_2 \sim t_3$ ):** The auxiliary switch  $S_a$  is turned off at  $t_2$ . The resonance among the resonant inductor  $L_r$ , the resonant capacitors  $C_{r1}$ ,  $C_{r2}$ ,  $C_{r5}$  and  $C_{ra}$  begins.  $C_{ra}$  is charged by  $L_r$ , while  $C_{r1}$ ,  $C_{r2}$  and  $C_{r5}$  are discharged by  $L_r$ . Stage 3 ends when the voltage across capacitors  $C_{r1}$ ,  $C_{r2}$  and  $C_{r5}$  is discharged to zero.

**Stage 4 (clamping,  $t_3 \sim t_4$ ):** the voltage of  $C_{r1}$ ,  $C_{r2}$  and  $C_{r5}$  is resonated to zero.  $D_1$ ,  $D_2$  and  $D_5$  turn on at  $t_3$ .  $u_{dc}$  is clamped to zero. The ZVS turn-on condition of main switches  $S_1$ ,  $S_2$  and  $S_5$  is achieved. Stage 4 ends when all main switches are turned on by ZVS SPWM.

**Stage 5 (short-circuit,  $t_4 \sim t_5$ ):** all main switches are ZVS turned on by short-circuit signal at  $t_4$ . The resonant inductor starts to store energy, the current in  $L_r$  increases linearly. The duration of Stage 5 ( $t_4 \sim t_5$ ) must be long enough to satisfy the ZVS condition. By the end of this stage, the current of  $L_r$   $i_{Lr}$  reaches  $i_{sc}$ . Stage 5 ends when main switches  $S_2$ ,  $S_4$  and  $S_6$  are turned off by ZVS SPWM.

**Stage 6 (resonance,  $t_5 \sim t_6$ ):**  $S_2$ ,  $S_4$  and  $S_6$  are turned off at  $t_5$ . Then there begins a resonance among the resonant inductor  $L_r$ , the resonant capacitors  $C_{r2}$ ,  $C_{r4}$ ,  $C_{r6}$  and  $C_{ra}$ .  $C_{ra}$  is discharged,  $C_{r2}$ ,  $C_{r4}$  and  $C_{r6}$  are charged by  $L_r$ . Stage 6 ends when the voltage across capacitor  $C_{ra}$  is discharged to zero.

**Stage 7 (clamping,  $t_6 \sim t_7$ ):** the voltage across capacitor  $C_{ra}$  is discharged to zero at  $t_6$ . The ZVS on condition of auxiliary switch  $S_a$  is achieved. Stage 7 ends when the auxiliary switch  $S_a$  is turned on by ZVS SPWM.

**Stage 8 ( $t_7$ ):** The auxiliary switch  $S_a$  is zero-voltage turned on at  $t_7$ . At the end of this stage, the commutation from  $D_6$  to  $S_5$  and  $D_4$  to  $S_1$  is finished. ZVS turn-on of both main switches and auxiliary switch realizes.

From  $t_7$  to  $t_8$ , the commutation from MOSFET to body diode of  $S_3$  to  $D_2$  and  $S_5$  to  $D_6$  is triggered by PWM signal, and these processes do not need to resonant  $u_{dc}$  to zero.

To realize ZVS turn-on of all switches, the short-circuit current  $i_{sc}$  in Stage 5 should meet certain conditions, and can be derived as follows:

The clamping capacitors voltage  $u_{Cc}$  can be obtained by using the voltage-second balance principle of the resonant inductor:

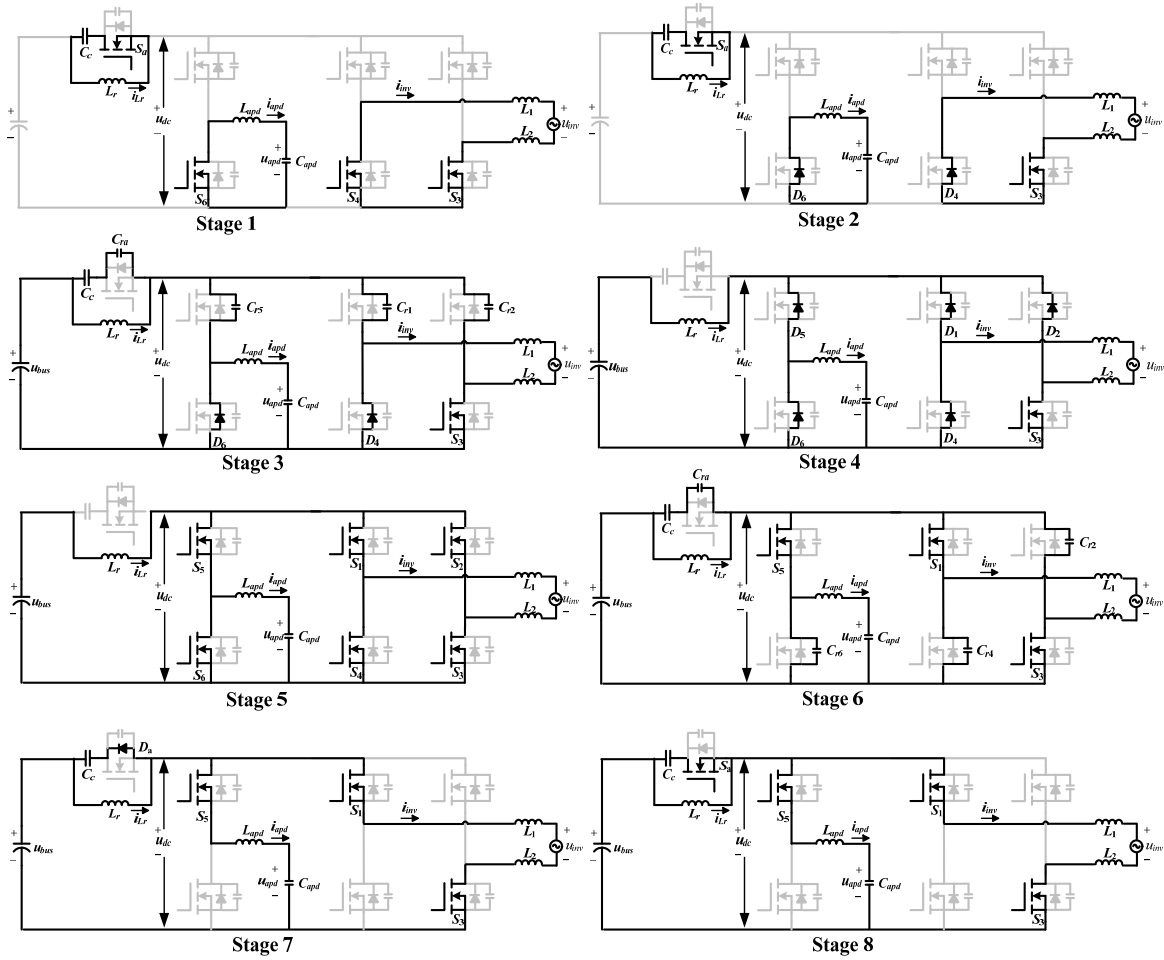


Fig. 7. Equivalent circuits of ZVS stages

$$u_{Cc} = \frac{1-D_a}{D_a} u_{bus} \quad (3)$$

Where  $D_a$  is the duty cycle of  $S_a$ . In order to reduce the voltage stress of all switches,  $u_{Cc}$  is always designed much smaller than  $u_{bus}$ .

The paralleled capacitors meet the following assumption:

$$C_{r1} = C_{r2} = C_{r3} = C_{r4} = C_{r5} = C_{r6} = C_{rm} = C_{ra} \quad (4)$$

The equivalent circuit of the first resonance progress (Stage 3) in Region I is shown in Fig. 9 (a), and its simplified equivalent circuit is shown in Fig. 9 (b).

In Fig. 9 (b),  $i_{rs1}$  is defined as the current that flows through dc bus at  $t_2$ . Its value is given in Table II. The definition of  $i_{rs1}$  simplifies later derivations.

TABLE II VALUE OF  $i_{rs1}$  AND  $i_{rs2}$

Mode	With APD		Without APD
	$i_{apd} > 0$	$i_{apd} < 0$	
$i_{rs1}$	0	$i_{apd}$	0
$i_{rs2}$	$i_{apd} +  i_{inv} $	$ i_{inv} $	$ i_{inv} $

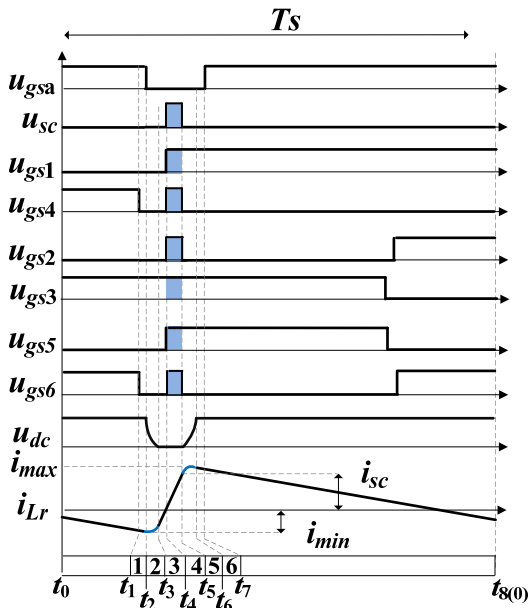


Fig. 8. Key waveforms of ZVS inverter with APD

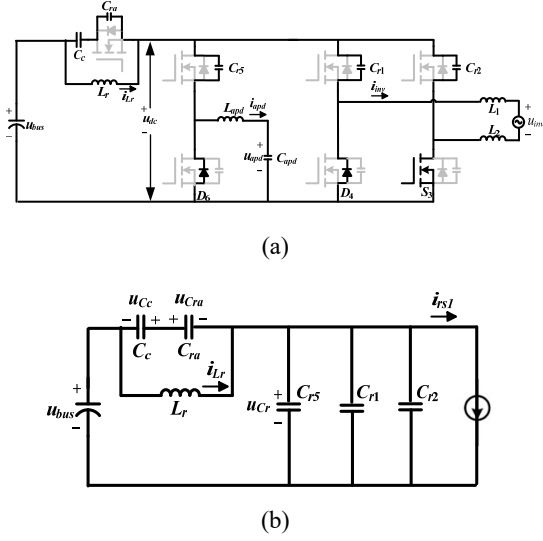


Fig. 9. (a) Equivalent circuit and (b) simplified equivalent circuit of first resonance progress from  $t_2$  to  $t_3$

The resonant equation of this stage is:

$$\begin{cases} u_{Cr}(t) = u_{Cc} \cos \omega_r t + [i_{min} - i_{rs1}] Z_r \sin \omega_r t + u_{bus} \\ i_{Lr}(t) = -\frac{u_{Cc}}{Z_r} \sin \omega_r t + [i_{min} - i_{rs1}] \cos \omega_r t + i_{rs1} \end{cases} \quad (5)$$

$$\text{where } \omega_r = 1/\sqrt{L_r C_r}, \quad Z_r = \sqrt{L_r/C_r}, \quad C_r = 3C_{rm} + C_{ra} \quad (6)$$

$i_{min}$  is the initial resonant current of  $L_r$ ,  $C_{rm}$  is the paralleled capacitance of main switches. The minimum value of  $u_{Cr}(t)$  in (5) must be less than zero to realize the ZVS on operation. We have:

$$i_{min} \leq -\sqrt{\frac{u_{bus}^2 - u_{Cc}^2}{Z_r^2}} + i_{rs1} \quad (7)$$

The equivalent circuit of the second resonance progress (Stage 6) in Region I is shown in Fig. 10 (a), and its simplified equivalent circuit is shown in Fig. 10 (b).

Like the definition of  $i_{rs1}$ ,  $i_{rs2}$  is defined as the current that flows through dc bus at  $t_5$ . Its value is given in Table II.

The resonant equation of this stage is:

$$\begin{cases} u_{Cra}(t) = u_{Cc} + u_{bus} \cos \omega_r t - (i_{sc} - i_{rs2}) Z_r \sin \omega_r t \\ i_{Lr}(t) = \frac{u_{bus}}{Z_r} \sin \omega_r t + (i_{sc} - i_{rs2}) \cos \omega_r t + i_{rs2} \end{cases} \quad (8)$$

$i_{sc}$  is the short-circuit current of  $L_r$ . The minimum value of  $u_{Cra}(t)$  in Eq. (8) must be less than zero to realize the ZVS on of  $S_a$ :

$$u_{Cc} \leq \sqrt{u_{bus}^2 + (i_{sc} - i_{rs2})^2 Z_r^2} \quad (9)$$

(9) is permanently established because  $u_{Cc} \ll u_{bus}$ . At the end of Stage 6, the current of  $L_r$   $i_{Lr}$  reaches its maximum value  $i_{max}$ :

$$i_{max} = \sqrt{\frac{u_{bus}^2 - u_{Cc}^2}{Z_r^2} + (i_{sc} - i_{rs2})^2} + i_{rs2} \quad (10)$$

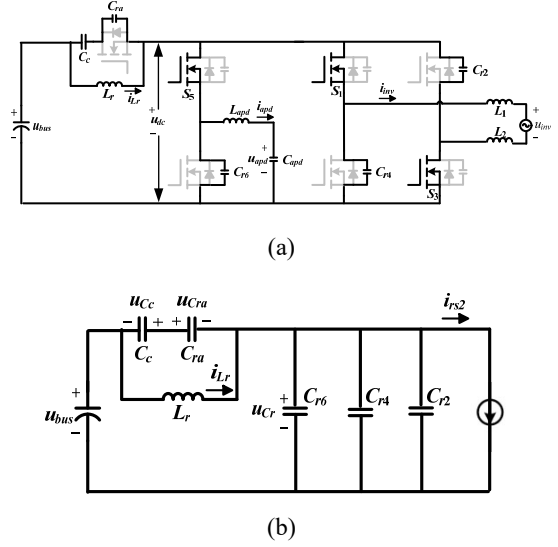


Fig. 10. (a) Equivalent circuit and (b) simplified equivalent circuit of second resonance progress from  $t_5$  to  $t_6$

The average current through the clamping capacitor  $C_c$  in a switching period should be zero according to the ampere-second balance of  $C_c$ . Therefore, the average current through  $L_r$  should be equal to the input current of DC link:

$$\frac{i_{max} + i_{min}}{2} \approx i_{dc} = \frac{p_0}{u_{bus}} \quad (11)$$

Where  $p_0 = u_{bus} i_{dc}$  is the total output power.

Combining (7), (10) with (11), the short-circuit current  $i_{sc}(t)$  should satisfy following condition:

$$i_{sc} \geq \sqrt{\left[2 \frac{p_0}{u_{bus}} - i_{rs1} - i_{rs2}\right]^2 + 4 \frac{p_0}{Z_r} - 2 \frac{u_{bus}}{Z_r} [i_{rs1} + i_{rs2}] + i_{rs2}} \quad (12)$$

#### IV. RESONANT PARAMETER DESIGN

An 1.5kW inverter prototype is designed to verify the theoretical derivation. The DC input voltage is 380V and the modulation ratio 0.82 (output voltage is RMS 220V). The switching frequency of inverter stage is 250kHz and the switching frequency of APD stage is 500kHz. The output ripple frequency is 500 kHz. The resonant parameters design is discussed as follows [10].

##### A. Duty cycle of $S_a$

$S_a$  is turned off from Stage 3 to Stage 6 and the duty cycle of  $S_a$  can be derived as:

$$D_a \approx 1 - L_r \frac{i_{max} - i_{min}}{u_{bus} T_s} \quad (13)$$

where  $T_s$  is the switching period.

The voltage of DC bus voltage in Stage 4 and Stage 5 is clamped to zero and the energy cannot be delivered from DC link to the load. The duty cycle of auxiliary switch  $S_a$  is expected to be greater than 0.85 to minimize duty cycle loss.

##### B. Resonant time

The duration of Stage 3 ( $t_2 \sim t_3$ ) and Stage 6 ( $t_5 \sim t_6$ ) must be longer than one fourth of a resonant period to guarantee the

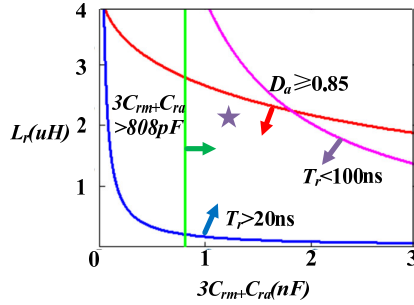


Fig. 11. Resonant parameter design region

completion of a resonant progress. The resonant time  $T_r$  is designed to be longer than the turn-off time of SiC MOSFET to reduce the turn-off loss, which is less than 20 ns. Its upper limit is expected to be less than 100 ns when  $T_s = 2 \mu s$  to reduce the duty cycle loss. So the limit of the resonant time is given by:

$$20ns \leq T_r = \frac{\pi\sqrt{L_r(3C_{rm}+C_{ra})}}{2} \leq 100ns \quad (14)$$

### C. Selection of resonant capacitor

SiC-MOSFET C2M0080120D used has output capacitance  $C_{oss}$  of 202 pF. So the resonant capacitance has a lower limit:

$$3C_{rm} + C_{ra} \geq 4C_{oss} = 808pF \quad (15)$$

Combining above mentioned design rules, the solution region can be determined as shown in Fig. 11. Finally the resonant inductor  $L_r$  is chosen as 2.2 uH and each paralleled capacitor for the main switches is 100pF. The auxiliary switch has no external paralleled resonant capacitor.

TABLE III SPECIFICATION OF PROTOTYPE

$u_{bus}$	380V
inverter modulation ratio	0.82
$f_s$	500kHz
$C_{dc}$	20uF
$C_{apd}$	125uF
MOSFET	C2M0080120D
$L_r$	2.2uH
$C_c$	33uF
$C_{r1} \sim C_{r6}$	100pF
$L_1 \& L_2$	50uH
$C_{inv}$	470nF
$L_{apd}$	175uH
$R_o$	32Ω / 46Ω / 95Ω

## V. EXPERIMENTAL RESULTS

The circuit and control diagram are shown in Fig. 12. The specification of the prototype is presented in Table. III. The prototype operates with RLC load. The duty ratio of inverter  $d_{inv}$  and the duty ratio of APD  $d_{apd}$  are calculated by inverter control loop and APD control loop [5] respectively.  $i_{sc}$  is

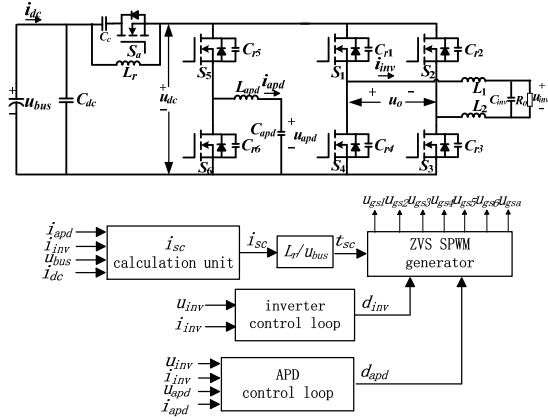


Fig. 12. Experimental circuit and control diagram

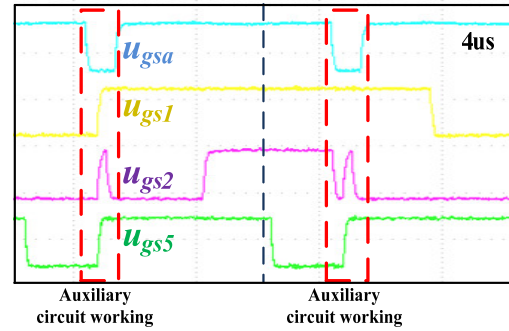


Fig. 13. ZVS SPWM modulation drive signals

calculated by  $i_{sc}$  calculation unit using (12). The short-circuit time  $t_{sc}$  ( $t_5 - t_4$  in Fig. 8) is calculated using

$$t_{sc} = L_r \frac{i_{sc}}{u_{bus}} \quad (16)$$

$d_{inv}$ ,  $d_{apd}$  and  $t_{sc}$  are sent to ZVS SPWM generator to form the drive signals of  $u_{gs1} \sim u_{gs6}$  and  $u_{gsa}$ .

Fig. 13 shows the drive signals of  $S_a$ ,  $S_1$ ,  $S_2$  and  $S_5$  in Region I. It can be seen that the drive signal of APD stage ( $S_5$ ) is synchronized with inverter stage ( $S_1$ ,  $S_2$ ) and the auxiliary switch ( $S_a$ ).

Fig. 14 (a) shows the theoretical resonant inductor short-circuit current  $i_{sc}$ , the theoretical maximum resonant inductor current  $i_{max}$  and the theoretical minimum resonant inductor current  $i_{min}$  of every switching cycle during one fundamental period under 1.5kW operation. Fig. 14 (b) shows the experimental resonant inductor current  $i_{Lr}(t)$  during one fundamental period. With control of short-circuit current  $i_{sc}(t)$ , the maximum and minimum current of resonant inductor  $i_{Lr}(t)$  meet the theoretical analysis.

Fig. 15 shows inverter voltage  $u_{inv}$  and input current  $i_{dc}$  without APD (a) and with (b) APD. It can be seen that the double-line frequency current ripple is greatly reduced with the APD stage.

Fig. 16 shows the resonant inductor current  $i_{Lr}$ , the DC-link voltage  $u_{dc}$ , the drain-source voltage of  $S_6$   $u_{ds6}$ , the output voltage of inverter stage  $u_o$  at different inverter output phase. The DC-link voltage  $u_{dc}$  is resonated to zero in each switching period. The duty ratio of both APD stage and inverter stage

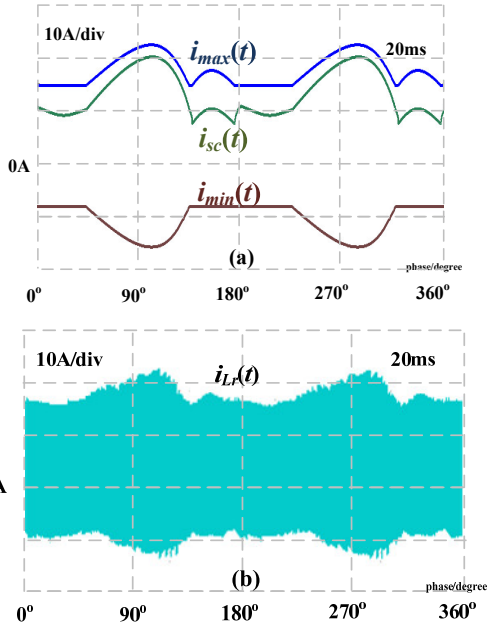


Fig. 14. (a) Theoretical and (b) experimental resonant inductor current

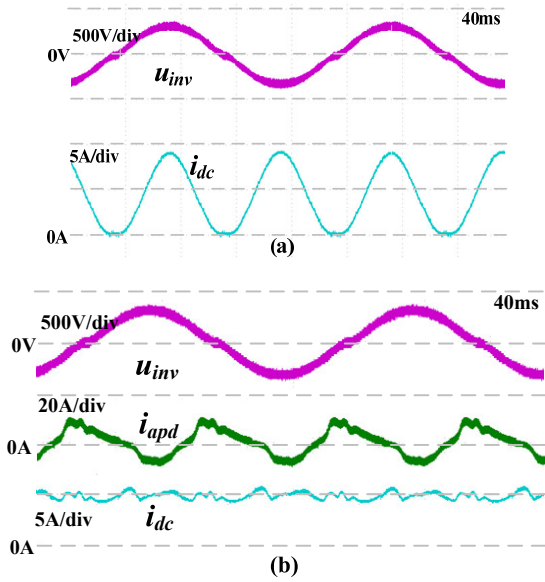
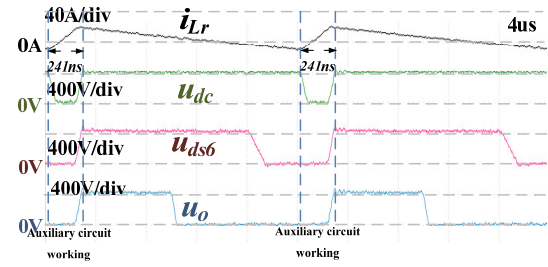


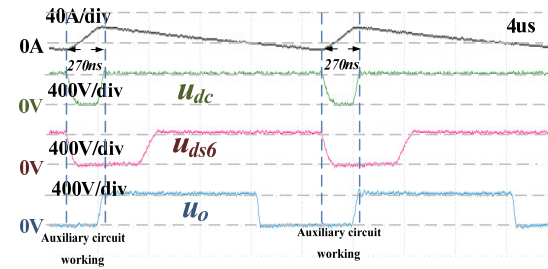
Fig. 15. (a) inverter voltage  $u_{inv}$  and input current  $i_{dc}$  without APD (b) inverter voltage  $u_{inv}$ , APD inductor current  $i_{apd}$  and input current  $i_{dc}$  with APD

with ZVS SPWM remains the same with traditional PWM. The working time of auxiliary circuit varies because  $t_{sc}$  changes with different output phase. According to Table I, if  $i_{apd}$  is positive (at  $30^\circ$  &  $150^\circ$ ), the commutation of APD stage needs ZVS is  $D_6$  to  $S_5$ , the turn-off of  $D_6$  accomplishes during the zero-voltage state of the DC link, as shown in Fig. 16(a) and (d). If  $i_{apd}$  is negative (at  $60^\circ$  &  $120^\circ$ ), the commutation of APD stage needs ZVS is  $D_5$  to  $S_6$ , so the falling edge of  $u_{ds6}$  is aligned with the falling edge of  $u_{dc}$ .

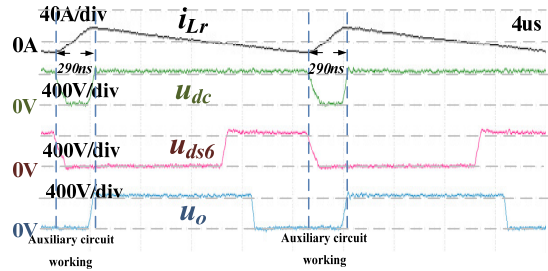
The drive signal of APD switch  $u_{gs5}$ , the drain-source voltage of  $S_5$   $u_{ds5}$  and the drain-source voltage of  $S_2$   $u_{ds2}$  with output phase of  $30^\circ$  (Region I) is shown in Fig.17 (a), and the driver signal of auxiliary switch  $u_{gsa}$  and drain-source voltage  $u_{dsa}$  is shown in Fig. 17 (b). The drive signals of  $S_5$  and  $S_a$  rise



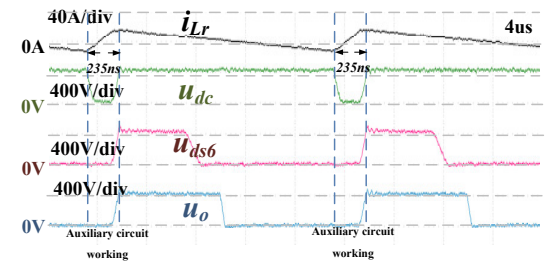
(a)  $30^\circ$  (Region I)



(b)  $60^\circ$  (Region II)



(c)  $120^\circ$  (Region II)



(d)  $150^\circ$  (Region I)

Fig. 16. Resonant inductor current  $i_{Lr}$ , dc-link voltage  $u_{dc}$ , drain-source voltage of  $S_6$   $u_{ds6}$ , inverter output voltage  $u_o$  with different inverter output phase, (a)  $30^\circ$ , (b)  $60^\circ$ , (c)  $120^\circ$ , (d)  $150^\circ$

after their drain-source voltage is resonated to zero respectively, and ZVS on is realized. The drive signal of APD switch  $u_{gs6}$ , the drain-source voltage of  $S_6$   $u_{ds6}$  and the drain-source voltage of  $S_2$   $u_{ds2}$  with output phase of  $60^\circ$  (Region II) is shown in Fig. 18 (a), and the driver signal of auxiliary switch  $u_{gsa}$  and drain-source voltage  $u_{dsa}$  is shown in Fig. 18 (b). The drive signals of  $S_6$  and  $S_a$  rise after their drain-source voltage is resonated to zero respectively, and ZVS on is realized.

The efficiency comparison under different load conditions between soft-switching and hard-switching is shown in Fig.19. The efficiency of ZVS inverter with APD is higher than hard-

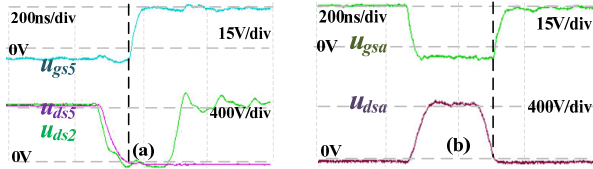


Fig. 17. ZVS realization with 30° inverter output phase (a) main switches, (b) auxiliary switch

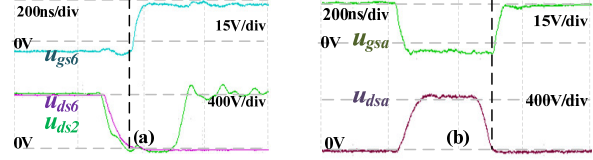


Fig. 18. ZVS realization with 60° inverter output phase (a) main switches, (b) auxiliary switch

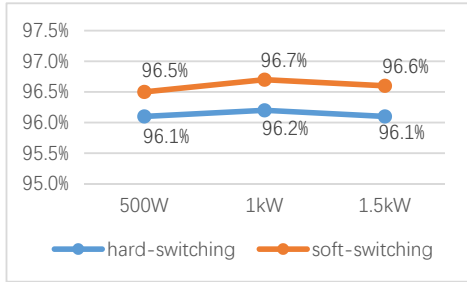


Fig. 19. Measured efficiency of ZVS single-phase inverter with APD

switching inverter under different load conditions, and the highest efficiency of soft-switching is 96.8% under 1kW load condition.

## VI. DISCUSSION

The commutation from the MOSFET to the body diode in Fig.4 (b) can realize ZVS turn-on of MOSFET with sufficient dead time. However, the conduction loss of SiC MOSFET's body diode during the dead time is not negligible due to higher voltage drop of the body diode. Shorter dead time can reduce the conduction loss of the body diode, however the turn-off of MOSFET may not be finished with small load current. As shown in Fig.20 (a), the turn-off of  $S_6$  is still proceeding and  $S_5$  is hard-switching turned on at the end of dead time, which happens when instant load current is near zero. Longer dead time ensures ZVS turn-on, shown in Fig.20 (b), but increases conduction loss of the body diode. During the current commutation from the MOSFET to the body diode, dead time needs to be carefully selected when  $i_{apd}$  and  $i_{inv}$  are near zero. The tradeoff between the conduction loss of body diode and switching loss will be considered in the future work.

The inverter stage operates in open-loop mode with fixed modulation ratio. The short-circuit time  $t_{sc}$  is pre-calculated using ideal conditions with theoretically  $i_{apd}$  and zero  $i_{dc}$  ripple. According to Fig.15 (b), in the experiment APD inductor current  $i_{apd}$  is not fully sinusoidal, and there is current ripple in  $i_{dc}$ . Therefore, the ZVS turn-on condition is not fully realized at some phase degrees, which causes higher loss. To realize ZVS conditions in all range, close-loop control of inverter and real-time computation of short circuit time  $t_{sc}$  is needed. In addition, the resonant inductor should be more carefully designed to minimize inductor loss due to its flowing current  $i_{Lr}$  with high frequency and high amplitude.

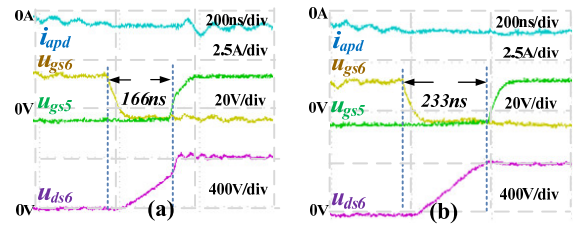


Fig. 20. Commutation from the MOSFET to the body diode (a) with shorter dead time,  $S_5$  hard-switching turned on, (b) with longer dead time,  $S_5$  ZVS turned on

## VII. CONCLUSION

A ZVS modulation scheme for single-phase inverter with APD is proposed. The stage analysis is provided and the ZVS condition is derived. The theoretical analysis is verified on a 500 kHz 1.5kW prototype with RLC load with open loop control. The double-line frequency ripple of DC input current is reduced and ZVS is realized.

Up to now, the conversion efficiency is lower than we expect. Further study is required such as operation range vs. ZVS condition. Since the APD inductor current waveform is not sinusoidal, it affects the ZVS switching condition of APD leg. There is higher loss in resonant inductor and its optimization is needed.

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